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**U.S. UTILITY Patent Application**

**O.I.P.E.**

**PATENT DATE**

APPLICATION NO. 09/945247	CONT/PRIOR F	CLASS 257 438	SUBCLASS 197	ART UNIT 2811 2811	EXAMINER J. M. MCGEE
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APPLICANTS

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## Method for fabrication of field effect transistors

PTO-2040  
12/99

## **ISSUING CLASSIFICATION**

Continued on Issue Slip Inside File Jacket

TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.				<b>NOTICE OF ALLOWANCE MAILED</b>	
<input checked="" type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____  _____  _____				<b>ISSUE FEE</b>	
	(Primary Examiner)	(Date)		Amount Due	Date Paid
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